DATA SHEET



SILICON TRANSISTOR 2SD2402

NPN SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

The 2SD2402 is a transistor featuring high current capacitance in small dimension. This transistor is ideal for DC/DC converters and motor drivers.

FEATURES

- High current capacitance
- · Low collector saturation voltage
- · Complementary transistor with 2SB1571

$\begin{array}{c} 4.5 \pm 0.1 \\ 1.6 \pm 0.2 \\ \hline \\ 0.42 \\ \pm 0.00 \\ \hline \\ 3.0 \\ \hline \\ 3.0 \\ \hline \\ 3.0 \\ \hline \\ 3.0 \\ \hline \\ 0.41 \\ \pm 0.06 \\ \hline \\ 0.41 \\ \hline$

PACKAGE DRAWING (UNIT: mm)

Electrode Connection

E : Emitter C : Collector(Fin)

B : Base

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		50	V
Collector to emitter voltage	VCEO		30	V
Emitter to base voltage	Vebo		6.0	V
Collector current (DC)	IC(DC)		5.0	А
Collector current (pulse)	C(pulse)	$PW \le 10 \text{ ms}$ duty cycle $\le 50 \%$	8.0	A
Base current (DC)	B(DC)		0.2	А
Base current (pulse)	B(pulse)	PW ≤ 10 ms duty cycle ≤ 50 %	0.4	A
Total power dissipation	Рт	16 cm ² \times 0.7 mm ceramic board mounted	2.0	W
Junction temperature	Tj		150	°C
Storage temperature	Tstg		-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

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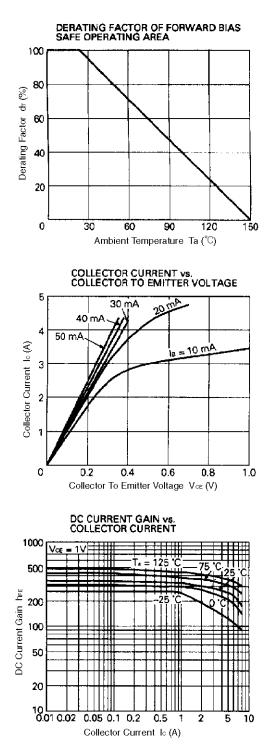
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

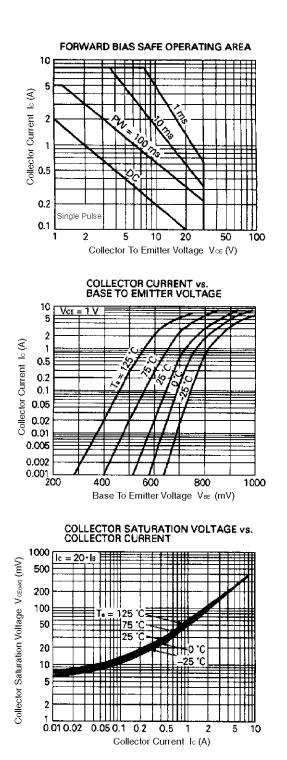
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$			100	nA
Emitter cutoff current	Іево	$V_{EB} = 6.0 \text{ V}, \text{ Ic} = 0$			100	nA
DC current gain	hfe1	Vce = 1.0 V, Ic = 1.0 A	80			-
DC current gain	hFE2	Vce = 1.0 V, Ic = 2.0 A	100	200	400	-
DC base voltage	VBE	Vce = 1.0 V, Ic = 0.1 A	600	650	700	mV
Collector saturation voltage	V _{CE(sat)1}	Ic = 3.0 V, Iв = 0.15 A		140	300	mV
Collector saturation voltage	V _{CE(sat)2}	Ic = 5.0 V, I _B = 0.25 A		230	500	mV
Base saturation voltage	V _{BE(sat)}	Ic = 3.0 V, I _B = 0.15 A		0.88	1.2	V
Gain bandwidth product	f⊤	Vce = 10 V, Ie = -0.5 A		170		MHz
Output capacitance	Cob	V _{CB} = 10 V, I _E = 0, f = 1 MHz		60		pF
Turn-on time	ton	Ic = 2.0 A, Vcc= 10 V		275		ns
Storage time	tstg	$I_{B1} = -I_{B2} = 0.1 \text{ A}$ $R_L = 500 \Omega$		485		ns
Fall time	tr			45		ns

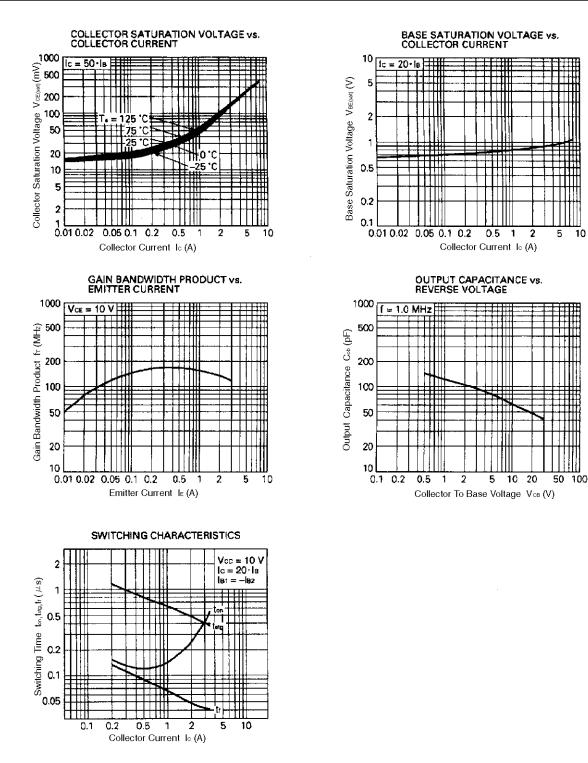
hfe CLASSIFICATION

Marking	EX	EY	EZ
hfe2	100 to 200	160 to 320	200 to 400

TYPICAL CHARACTERISTICS (Ta = 25°C)







[MEMO]

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